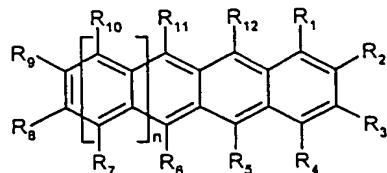


Claims

1. An organic semiconducting layer formulation, which comprises:
 an organic binder which has a permittivity, ϵ , at 1,000 Hz of 3.3 or less; and
 5 a polyacene compound of Formula A:



Formula A

wherein:

each of R₁, R₂, R₃, R₄, R₅, R₆, R₇, R₈, R₉, R₁₀, R₁₁ and R₁₂, which may be the same or different, independently represents hydrogen; an optionally substituted C₁-C₄₀ carbyl or hydrocarbyl group; an optionally substituted C₁-C₄₀ alkoxy group; an optionally substituted C₆-C₄₀ aryloxy group; an optionally substituted C₇-C₄₀ alkylaryloxy group; an optionally substituted C₂-C₄₀ alkoxycarbonyl group; an optionally substituted C₇-C₄₀ aryloxycarbonyl group; a cyano group (-CN); a carbamoyl group (-C(=O)NH₂); a haloformyl group (-C(=O)-X, wherein X represents a halogen atom); a formyl group (-C(=O)-H); an isocyano group; an isocyanate group; a thiocyanate group or a thioisocyanate group; an optionally substituted amino group; a hydroxy group; a nitro group; a CF₃ group; a halo group (Cl, Br, F); or an optionally substituted silyl group; and

wherein independently each pair of R₂ and R₃ and/or R₈ and R₉, may be cross-bridged to form a C₄-C₄₀ saturated or unsaturated ring, which saturated or unsaturated ring may be intervened by an oxygen atom, a sulphur atom or a group shown by formula -N(R_a)- (wherein R_a is a hydrogen atom or an optionally substituted hydrocarbon group), or may optionally be substituted; and

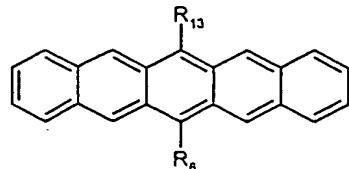
wherein one or more of the carbon atoms of the polyacene skeleton may optionally be substituted by a heteroatom selected from N, P, As, O, S, Se and Te; and wherein independently any two or more of the substituents R₁-R₁₂ which are located on adjacent ring positions of the polyacene may, together, optionally constitute a further C₄-C₄₀ saturated or unsaturated ring optionally interrupted by O, S or -N(R_a) where R_a is as defined above) or an aromatic ring system, fused to the polyacene; and wherein

n is 0, 1, 2, 3 or 4.

2. An organic semiconducting layer formulation as claimed in claim 1 wherein the

polyacene compound is selected from Compound Groups 1 or 8 or isomers thereof wherein:

compound Group 1 is represented by Formula 1:

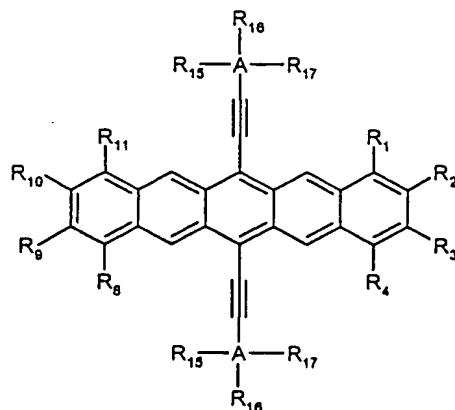


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Formula 1

and

compound Group 8 is represented by Formula 8:



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Formula 8

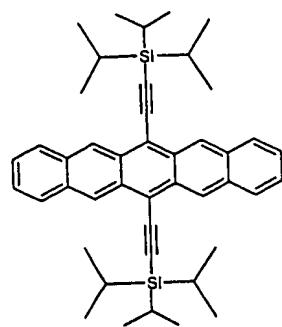
wherein, R₆ and R₁₃ in Group 1 and R₁, R₂, R₃, R₄, R₈, R₉, R₁₀, R₁₁, R₁₅, R₁₆, R₁₇ and R₁₈, in Group 8 are each independently the same or different and each independently represents: H; an optionally substituted C₁-C₄₀ carbyl or hydrocarbyl group; an optionally substituted C₁-C₄₀ alkoxy group; an optionally substituted C₆-C₄₀ aryloxy group; an optionally substituted C₇-C₄₀ alkylaryloxy group; an optionally substituted C₂-C₄₀ alkoxy carbonyl group; an optionally substituted C₇-C₄₀ aryloxycarbonyl group; a cyano group (-CN); a carbamoyl group (-C(=O)NH₂); a haloformyl group (-C(=O)-X, wherein X represents a halogen atom); a formyl group (-C(=O)-H); an isocyano group; an isocyanate group; a thiocyanate group or a thioisocyanate group; an optionally substituted amino group; a hydroxy group; a nitro group; a CF₃ group; a halo group (Cl, Br, F); or an optionally substituted silyl group; and wherein independently each pair of R₁ and R₂, R₂ and R₃, R₃ and R₄, R₈ and R₉, R₉ and R₁₀, R₁₀ and R₁₁, R₁₅ and R₁₆ and R₁₆ and R₁₇ may be cross-bridged with each other to form a C₄-C₄₀ saturated or unsaturated ring, which saturated or unsaturated ring may be intervened by an oxygen atom, a sulphur atom or a group shown by formula: -N(R_a)- (wherein R_a is a hydrogen atom or a hydrocarbon group), or may optionally be substituted; and wherein A represents Silicon or Germanium.

3. An organic semiconducting layer formulation as claimed in claim 1 or 2 wherein n is 0 or 2.

4. An organic semiconducting layer formulation as claimed in claim 3 wherein n is 2.

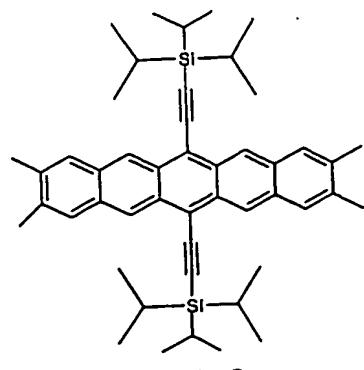
5. An organic semiconducting layer formulation as claimed in any of the preceding claims wherein the optionally substituted C₁-C₄₀ hydrocarbyl group is a saturated or unsaturated acyclic group, or a saturated or unsaturated cyclic group.

10 6. An organic semiconducting layer formulation as claimed in any of preceding claims 1 to 5 wherein the polyacene compound is 6, 13-bis(triisopropylsilyl)pentacene of Formula 1,



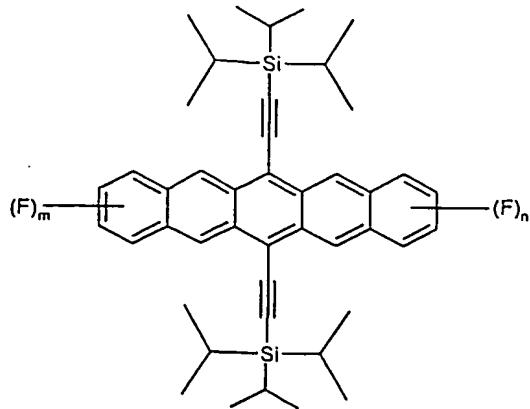
15 Formula 1

7. An organic semiconducting layer formulation as claimed in any of preceding claims 1 to 5 wherein the polyacene compound is 2,3,9,10-tetramethyl,6,13-bis (triisopropylsilyl)pentacene of Formula 2:



Formula 2

25 8. An organic semiconducting layer formulation as claimed in any of preceding 1 to 5 wherein the polyacene compound of Formula 3:



Formula 3

wherein n and m is each independently 0,1, 2, 3 or 4, more preferably 0,1 or 2;

5 9. An organic semiconducting layer formulation as claimed in any of the preceding claims wherein the organic binder resin has a permittivity at 1,000 Hz of less than 3.0, preferably 2.9 or less.

10 10. An organic semiconducting layer formulation as claimed in claim 10 wherein the organic binder resin has a permittivity at 1,000 Hz greater than 1.7, especially a permittivity from 2.0 to 2.9.

15 11. An organic semiconducting layer formulation as claimed in any one preceding claim wherein the organic binder resin is an insulating binder.

12. An organic semiconducting layer formulation as claimed in claim 11 wherein the insulating binder is selected from poly(α -methylstyrene), polyvinylcinnamate, poly(4-vinylbiphenyl), poly(4-methylstyrene) and TopasTM 8007, more preferably poly(α -methylstyrene), polyvinylcinnamate and poly(4-vinylbiphenyl).

20 13. An organic semiconducting layer formulation as claimed in any of claims 1 to 10 wherein the organic binder resin is a semiconductor binder.

25 14. An organic semiconducting layer formulation as claimed in claim 13 wherein the semiconductor binder comprises a number average molecular weight (M_n) of at least 1500-2000, more preferably at least 3000, even more preferably at least 4000 and most preferably at least 5000.

30 15. An organic semiconducting layer formulation as claimed in claims 13 or 14 wherein the semiconductor binder is selected from poly(9-vinylcarbazole) or PTAA1.

16. An organic semiconducting layer formulation as claimed in any of the preceding claims wherein the formulation further comprises a solvent.

17. An organic semiconducting layer formulation as claimed in any of the preceding 5 claims wherein the solvent is selected from xylene(s), toluene, tetralin and o-dichlorobenzene.

18. An organic semiconducting layer formulation as claimed in any of the preceding 10 claims wherein the ratio of polyacence compound to binder is 20:1 to 1:20 by weight, preferably 10:1 to 1:10 more preferably 5:1 to 1:5, still more preferably 3:1 to 1:3 further preferably 2:1 to 1:2 and especially 1:1.

19. An organic semiconducting layer formulation as claimed in any of the preceding 15 claims which comprises a solids content of 0.1 to 10% more preferably 0.5 to 5% by weight.

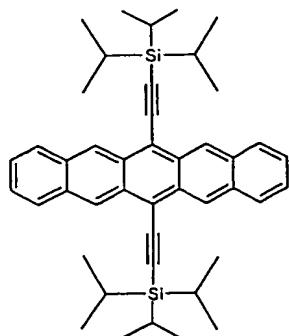
20. A process for preparing an organic semiconducting layer formulation as claimed in any of the preceding claims which comprises: (i) depositing on a substrate a liquid layer of a mixture which comprises the polyacene compound, the organic binder resin or precursor thereof and optionally a solvent, and (ii) forming from the liquid layer a solid layer which is the organic semiconducting layer.

21. An electronic device comprising an organic semiconducting layer formulation as claimed in any of preceding claims 1 to 19.

25 22. An electronic device according to claim 21 which comprises a field effect transistor (FET), organic light emitting diode (OLED), photodetector, chemical detector, photovoltaic cell (PVs), capacitor sensor, logic circuit, display or memory device.

30 23. An OFET device comprising an organic semiconducting layer formulation wherein the organic semiconducting layer formulation comprises:

- a compound of Formula 1;
- a binder; and
- a solvent,

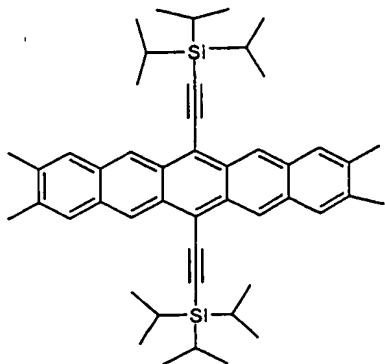


Formula 1

wherein the binder is selected from poly(α -methylstyrene), Topas™ 8007, poly(4-methylstyrene), polystyrene and polystyrene-co- α -methylstyrene, most preferably poly(α -methylstyrene); and the solvent is selected from toluene, ethylcyclohexane, anisole and p-xylene; most preferably toluene.

24. An OFET device comprising an organic semiconducting layer formulation wherein the organic semiconducting layer formulation comprises:

- 10 a compound of Formula 2;
- a binder; and
- a solvent,

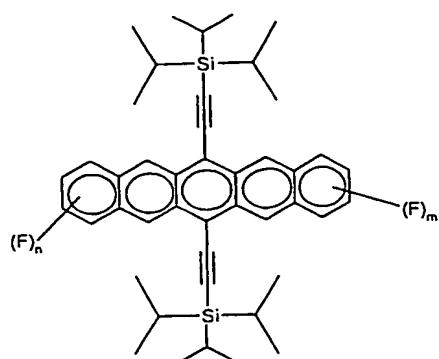


Formula 2

15 wherein the binder is selected from poly(α -methylstyrene), polyvinylcinnamate, and poly(4-vinylbiphenyl), most preferably poly(α -methylstyrene); and the solvent is 1,2-dichlorobenzene.

25. An OFET device comprising an organic semiconducting layer formulation wherein the organic semiconducting layer comprises:

- 20 a compound of Formula 3;
- a binder; and
- a solvent,



Formula (3)

wherein :

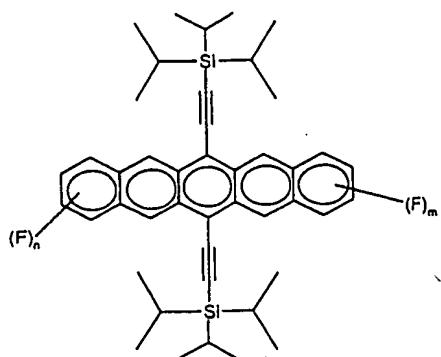
n and m are each independently 0, 1, 2, 3 or 4, more preferably 0, 1 or 2; and

5

the binder is poly(α -methylstyrene); and

the solvent is toluene.

26. A compound of Formula 3



10 wherein n and m are each independently 1 or 3, more preferably 1.